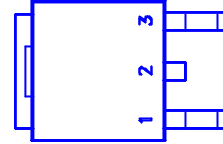
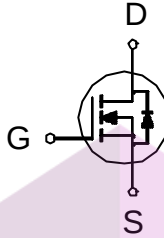


PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
40V	25m Ω	12A



1. GATE
2. DRAIN
3. SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	12	A
	$T_C = 100^\circ\text{C}$		10	
Pulsed Drain Current ¹		I_{DM}	45	
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	41	W
	$T_C = 100^\circ\text{C}$		32	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	$^\circ\text{C}$
Lead Temperature (l_{16} from case for 10 sec.)		T_L	275	

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		3	$^\circ\text{C} / \text{W}$
Junction-to-Ambient	$R_{\theta JA}$		75	$^\circ\text{C} / \text{W}$

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	40			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	2.0	3.0	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 32V, V_{GS} = 0V$			1	μA
		$V_{DS} = 30V, V_{GS} = 0V, T_C = 125^\circ C$			10	
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = 10V, V_{GS} = 10V$	45			A
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 10A$		35	45	mΩ
		$V_{GS} = 10V, I_D = 12A$		21	25	

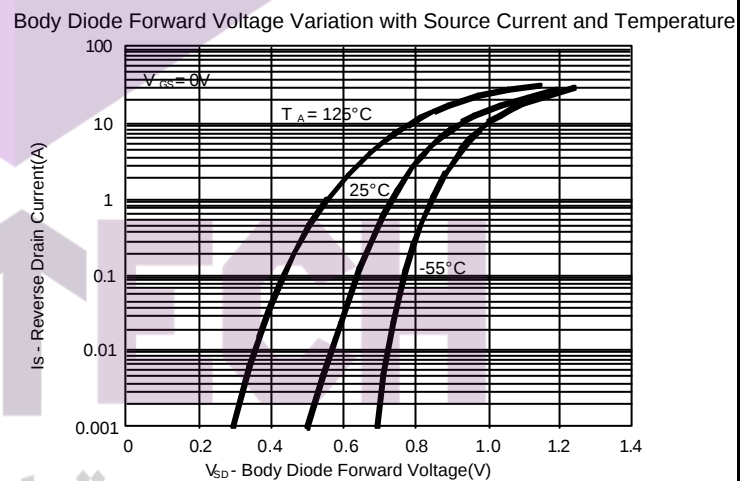
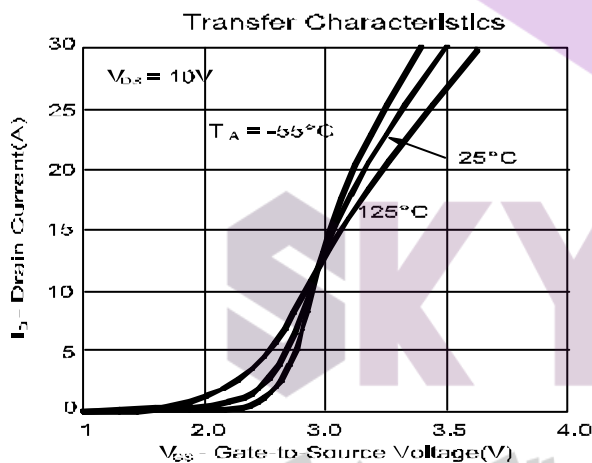
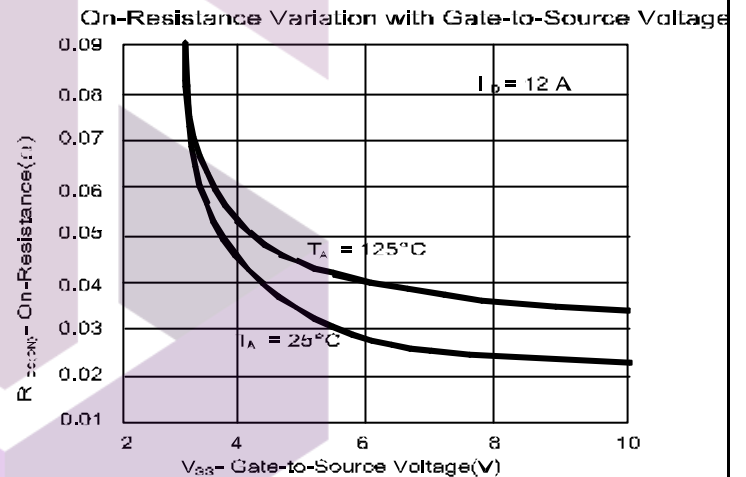
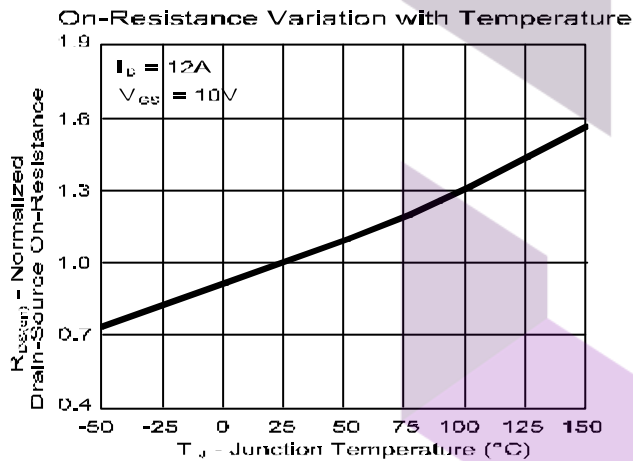
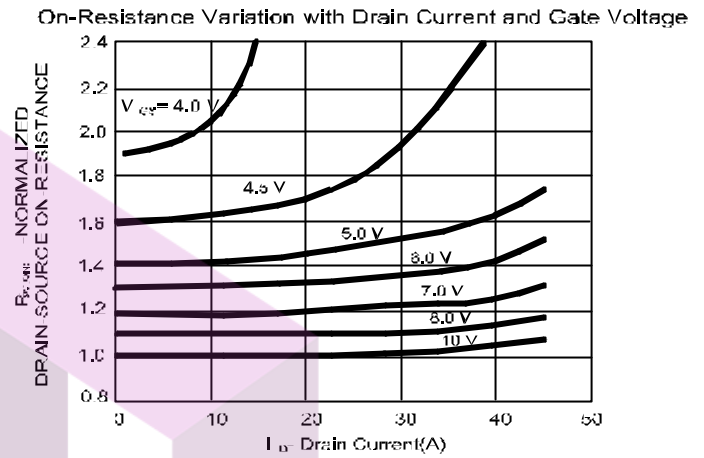
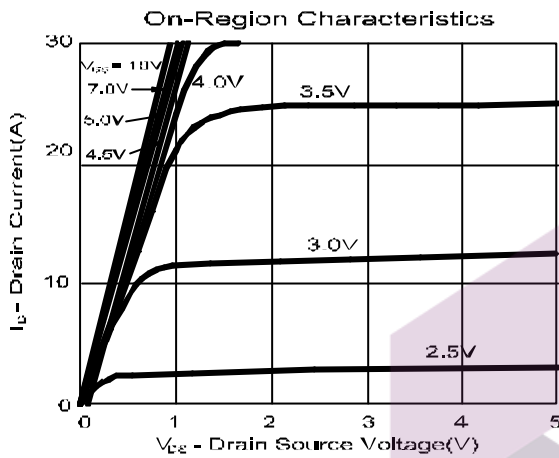
Forward Transconductance ¹	g_{fs}	$V_{DS} = 10V, I_D = 12A$		18		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 10V, f = 1MHz$		760		pF
Output Capacitance	C_{oss}			165		
Reverse Transfer Capacitance	C_{rss}			55		
Total Gate Charge ²	Q_g	$V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = 10V, I_D = 12A$		16		nC
Gate-Source Charge ²	Q_{gs}			2.5		
Gate-Drain Charge ²	Q_{gd}			2.1		
Turn-On Delay Time ²	$t_{d(on)}$	$V_{DS} = 20V, R_L = 1\Omega$ $I_D \cong 1A, V_{GS} = 10V, R_{GEN} = 6\Omega$		2.1	4.2	nS
Rise Time ²	t_r			7.2	14	
Turn-Off Delay Time ²	$t_{d(off)}$			11.6	21.0	
Fall Time ²	t_f			3.5	7.2	
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_c = 25^\circ C$)						
Continuous Current	I_S				12	A
Pulsed Current ³	I_{SM}				40	
Forward Voltage ¹	V_{SD}	$I_S = I_S, V_{GS} = 0V$			1.2	V
Reverse Recovery Time	t_{rr}	$I_F = 5 A, dI_F/dt = 100A / \mu S$		14.5		nS
Reverse Recovery Charge	Q_{rr}			7.2		nC

¹Pulse test : Pulse Width $\leq 300 \mu sec$, Duty Cycle $\leq 2\%$.²Independent of operating temperature.³Pulse width limited by maximum junction temperature.**REMARK: THE PRODUCT MARKED WITH "P2504BDG", DATE CODE or LOT #**

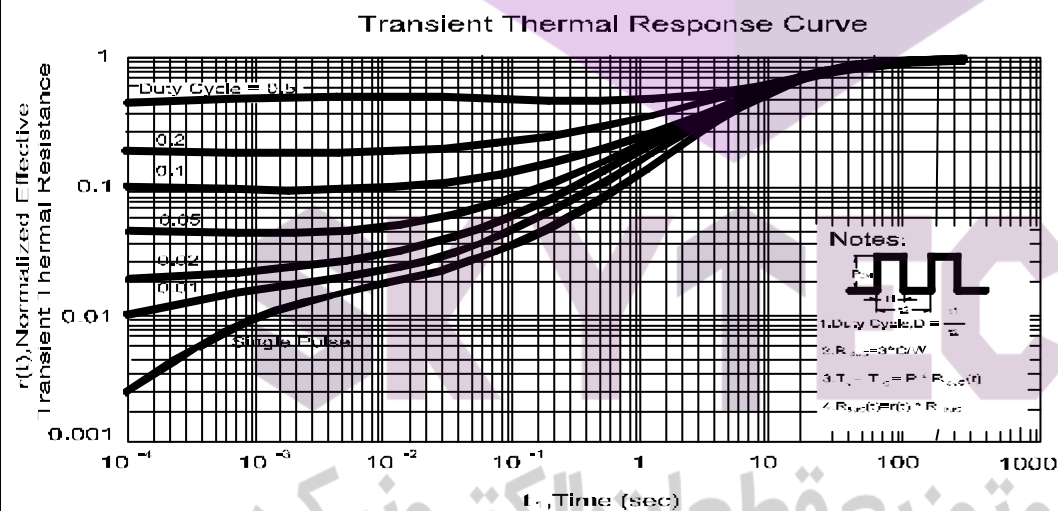
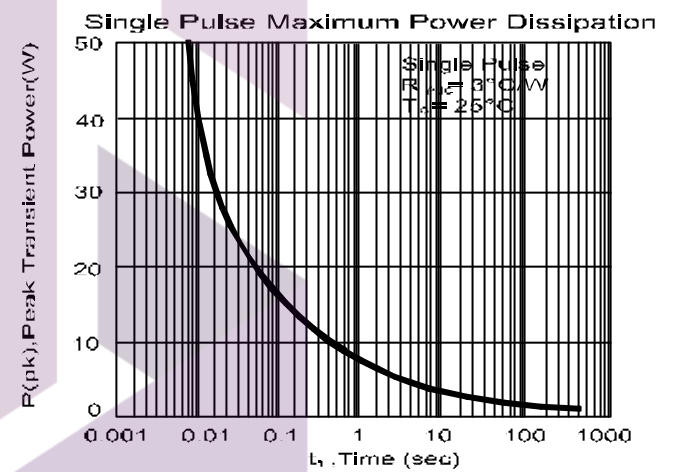
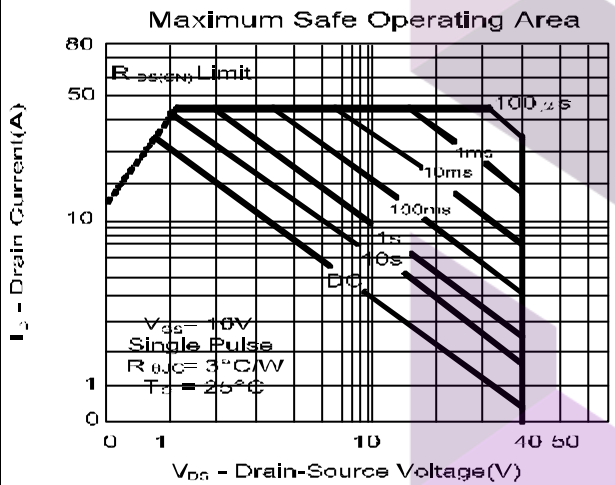
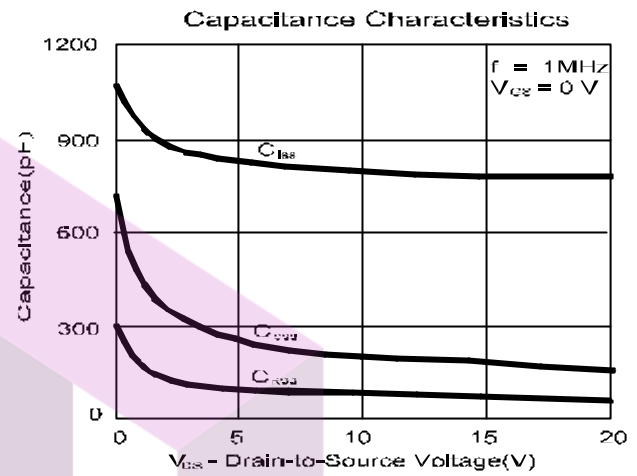
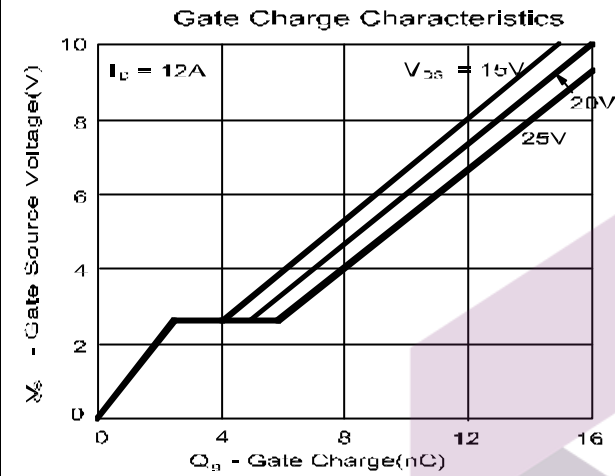
Orders for parts with Lead-Free plating can be placed using the PXXXXXXG parts name.

SKYTECH

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TO-252 (DPAK) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	9.35		10.1	H		0.8	
B	2.2		2.4	I	6.4		6.6
C	0.48		0.6	J	5.2		5.4
D	0.89		1.5	K	0.6		1
E	0.45		0.6	L	0.64		0.9
F	0.03		0.23	M	4.4		4.6
G	6		6.2	N			

